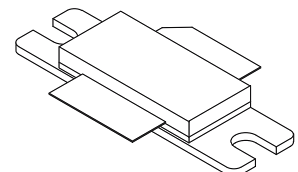
The RF MOSFET Line
RF Power Field Effect Transistors
N–Channel Enhancement–Mode Lateral MOSFETs

MRF19085
MRF19085R3
MRF19085SR3
MRF19085LSR3

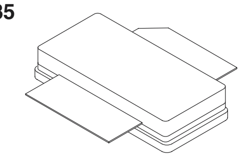
1990 MHz, 90 W, 26 V
LATERAL N–CHANNEL
RF POWER MOSFETs

Designed for PCN and PCS base station applications with frequencies from 1.9 to 2.0 GHz. Suitable for TDMA, CDMA and multicarrier amplifier applications.

- Typical 2–Carrier N–CDMA Performance for V_{DD} = 26 Volts, I_{DQ} = 850 mA, P_{out} = 18 Watts Avg., f1 = 1960 MHz, f2 = 1962.5 MHz IS–95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) 1.2288 MHz Channel Bandwidth Carrier. Adjacent Channels Measured over a 30 kHz Bandwidth at f1 –885 Khz and f2 +885 kHz. Distortion Products Measured over 1.2288 MHz Bandwidth at f1 –2.5 MHz and f2 +2.5 MHz. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF.
  Output Power — 18 Watts Avg.
  Power Gain — 13.0 dB
  Efficiency — 23%
  ACPR — –51 dB
  IM3 — –36.5 dBc
- Internally Matched, Controlled Q, for Ease of Use
- High Gain, High Efficiency and High Linearity
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Capable of Handling 5:1 VSWR, @ 26 Vdc, 1.93 GHz, 90 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large–Signal Impedance Parameters
- Available in Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 Inch Reel.
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40μ″ Nominal.



CASE 465–06, STYLE 1
NI–780
MRF19085



CASE 465A–06, STYLE 1
NI–780S
MRF19085SR3, MRF19085LSR3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	65	Vdc
Gate–Source Voltage	V_{GS}	–0.5, +15	Vdc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	273 1.56	Watts W/°C
Storage Temperature Range	T_{stg}	–65 to +200	°C
Operating Junction Temperature	T_J	200	°C

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.64	°C/W

NOTE – **CAUTION** – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

REV 4

MOTOROLA intelligence everywhere™ digital dna™

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 100 μAdc)	$V_{(BR)DSS}$	65	—	—	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 26 Vdc, V_{GS} = 0 Vdc)	I_{DSS}	—	—	10	μAdc
Gate–Source Leakage Current (V_{GS} = 5 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	—	—	1	μAdc
ON CHARACTERISTICS (DC)					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 200 μAdc)	$V_{GS(th)}$	2	—	4	Vdc
Gate Quiescent Voltage (V_{DS} = 26 Vdc, I_D = 850 mAdc)	$V_{GS(Q)}$	2.5	3.5	4.5	Vdc
Drain–Source On–Voltage (V_{GS} = 10 Vdc, I_D = 2 Adc)	$V_{DS(on)}$	—	0.18	0.210	Vdc
Forward Transconductance (V_{DS} = 10 Vdc, I_D = 2 Adc)	g_{fs}	—	6	—	S
DYNAMIC CHARACTERISTICS					
Reverse Transfer Capacitance (1) (V_{DS} = 26 Vdc, V_{GS} = 0, f = 1.0 MHz)	C_{rss}	—	3.6	—	pF
FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system) 2–Carrier N–CDMA, 1.2288 MHz Channel Bandwidth Carriers. Peak/Avg. Ratio = 9.8 dB @ 0.01% Probability on CCDF.					
Common–Source Amplifier Power Gain (V_{DD} = 26 Vdc, P_{out} = 18 W Avg., I_{DQ} = 850 mA, f1 = 1930 MHz, f2 = 1932.5 MHz and f1 = 1987.5 MHz, f2 =1990 MHz)	G_{ps}	12	13	—	dB
Drain Efficiency (V_{DD} = 26 Vdc, P_{out} = 18 W Avg., I_{DQ} = 850 mA, f1 = 1930 MHz, f2 = 1932.5 MHz and f1 = 1987.5 MHz, f2 =1990 MHz)	η	21	23	—	%
3rd Order Intermodulation Distortion (V_{DD} = 26 Vdc, P_{out} = 18 W Avg., I_{DQ} = 850 mA, f1 = 1930 MHz, f2 = 1932.5 MHz and f1 = 1987.5 MHz, f2 =1990 MHz); IM3 measured over 1.2288 MHz bandwidth @ f1 –2.5 MHz and f2 = +2.5 MHz)	IMD	—	–36.5	–35	dBc
Adjacent Channel Power Ratio (V_{DD} = 26 Vdc, P_{out} = 18 W Avg., I_{DQ} = 850 mA, f1 = 1930 MHz, f2 = 1932.5 MHz and f1 = 1987.5 MHz, f2 =1990 MHz); ACPR measured over 30 kHz bandwidth @ f1 –885 MHz and f2 =+885 MHz)	ACPR	—	–51	–48	dBc
Input Return Loss (V_{DD} = 26 Vdc, P_{out} = 18 W Avg., I_{DQ} = 850 mA, f1 = 1930 MHz, f2 = 1932.5 MHz and f1 = 1987.5 MHz, f2 =1990 MHz)	IRL	—	–12	–9	dB
Output Mismatch Stress (V_{DD} = 26 Vdc, P_{out} = 90 W CW, I_{DQ} = 850 mA, f = 1930 MHz, VSWR = 5:1, All Phase Angles at Frequency of Tests)	Ψ	No Degradation In Output Power Before and After Test			

(1) Part is internally matched both on input and output.

ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
FUNCTIONAL TESTS (In Motorola Test Fixture)					
Two–Tone Common–Source Amplifier Power Gain (V_{DD} = 26 Vdc, P_{out} = 90 W PEP, I_{DQ} = 850 mA, f = 1930 MHz and 1990 MHz, Tone Spacing = 100 kHz)	G_{ps}	—	13	—	dB
Two–Tone Drain Efficiency (V_{DD} = 26 Vdc, P_{out} = 90 W PEP, I_{DQ} = 850 mA, f = 1930 MHz and 1990 MHz, Tone Spacing = 100 kHz)	η	—	36	—	%
3rd Order Intermodulation Distortion (V_{DD} = 26 Vdc, P_{out} = 90 W PEP, I_{DQ} = 850 mA, f = 1930 MHz and 1990 MHz, Tone Spacing = 100 kHz)	IMD	—	–31	—	dBc
Input Return Loss (V_{DD} = 26 Vdc, P_{out} = 90 W PEP, I_{DQ} = 850 mA, f = 1930 MHz and 1990 MHz, Tone Spacing = 100 kHz)	IRL	—	–12	—	dB
P_{out}, 1 dB Compression Point (V_{DD} = 26 Vdc, I_{DQ} = 850 mA, f = 1990 MHz)	P1dB	—	90	—	W

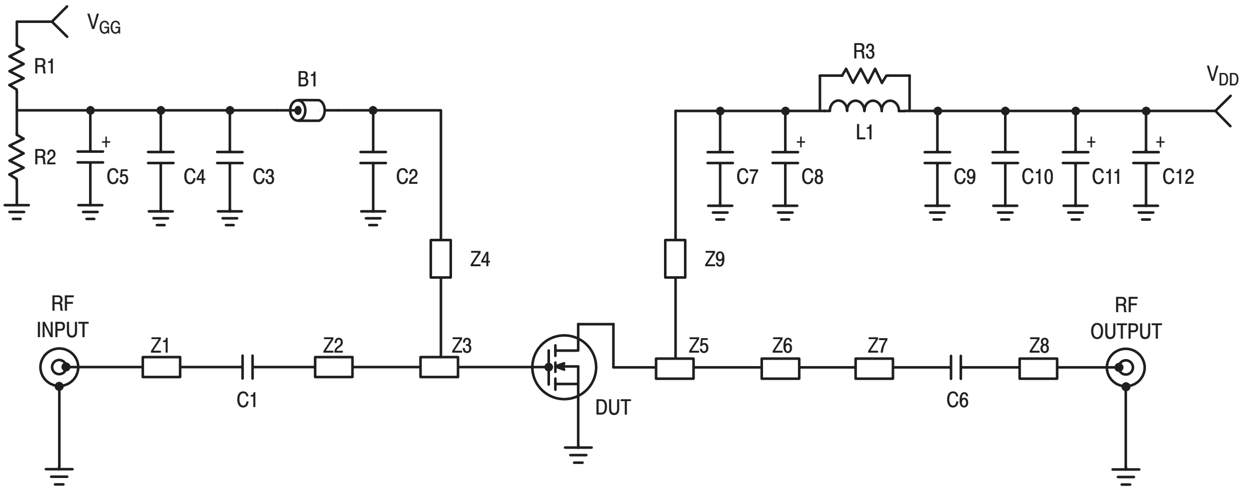


Figure 1. 1930 – 1990 MHz 2–Carrier N–CDMA Test Circuit Schematic

Table 1. 1930 – 1990 MHz 2–Carrier N–CDMA Test Circuit Component Designations and Values

Part	Description	Value, P/N or DWG	Manufacturer
B1	Short Ferrite Bead	2743019447	Fair Rite
C1	51 pF Chip Capacitor	100B510JCA500X	ATC
C2, C7	5.1 pF Chip Capacitors	100B5R1JCA500X	ATC
C3, C9	1000 pF Chip Capacitors	100B102JCA500X	ATC
C4, C10	0.1 μF Chip Capacitors	CDR33BX104AKWS	Kemet
C5	0.1 μF Tantalum Surface Mount Capacitor	T491C105M050	Kemet
C6	10 pF Chip Capacitor	100B100JCA500X	ATC
C8	10 μF Tantalum Surface Mount Capacitor	T495X106K035AS4394	Kemet
C11, C12	22 μF Tantalum Surface Mount Capacitors	T491X226K035AS4394	Kemet
L1	1 Turn, 20 AWG, 0.100″ ID		Motorola
N1, N2	Type N Flange Mounts	3052-1648-10	Omni Spectra
R1	1.0 kΩ, 1/8 W Chip Resistor		
R2	220 kΩ, 1/8 W Chip Resistor		
R3	10 Ω, 1/8 W Chip Resistor		
Z1	Microstrip	0.750″ x 0.0840″	
Z2	Microstrip	1.090″ x 0.0840″	
Z3	Microstrip	0.400″ x 1.400″	
Z4	Microstrip	0.520″ x 0.050″	
Z5	Microstrip	0.540″ x 1.133″	
Z6	Microstrip	0.400″ x 0.140″	
Z7	Microstrip	0.555″ x 0.0840″	
Z8	Microstrip	0.720″ x 0.0840″	
Z9	Microstrip	0.560″ x 0.070″	
Board	0.030″ Glass Teflon®	GX-0300-55-22, ε_r = 2.55	Keene
PCB	Etched Circuit Boards	MRF19085 Rev. 4	CMR

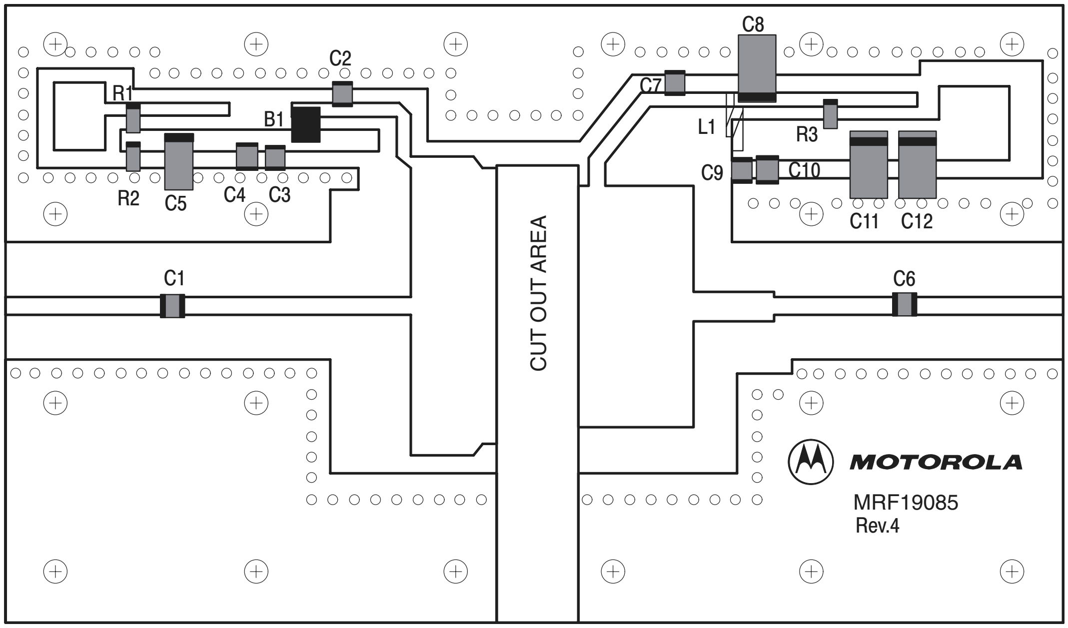


Figure 2. 1930 – 1990 MHz 2–Carrier N–CDMA Test Circuit Component Layout

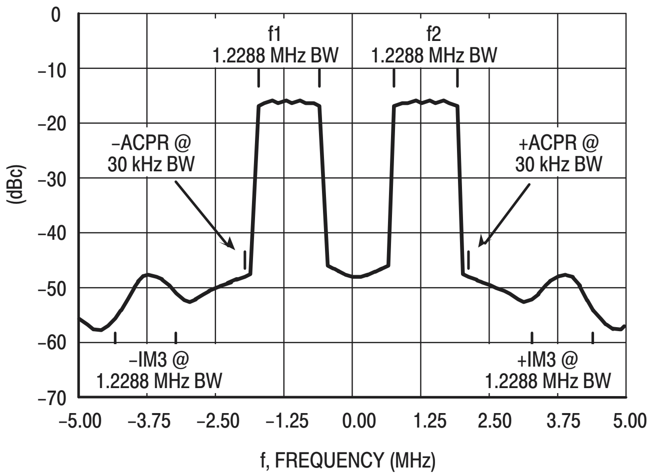


Figure 3. 2-Carrier N-CDMA Spectrum

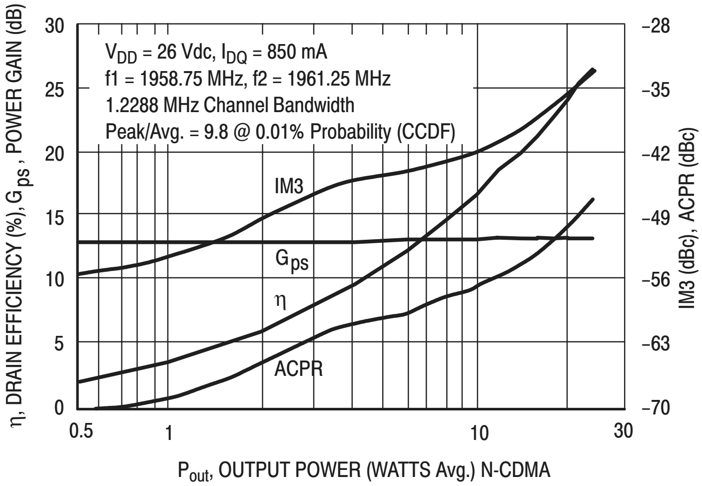


Figure 4. 2-Carrier N–CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

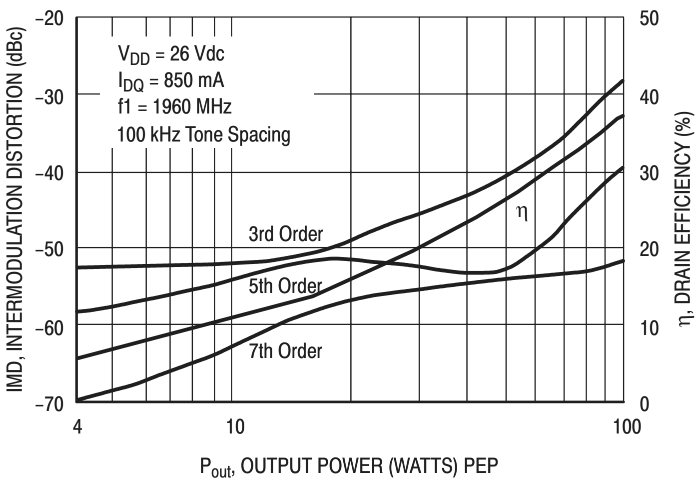


Figure 5. Intermodulation Distortion Products versus Output Power

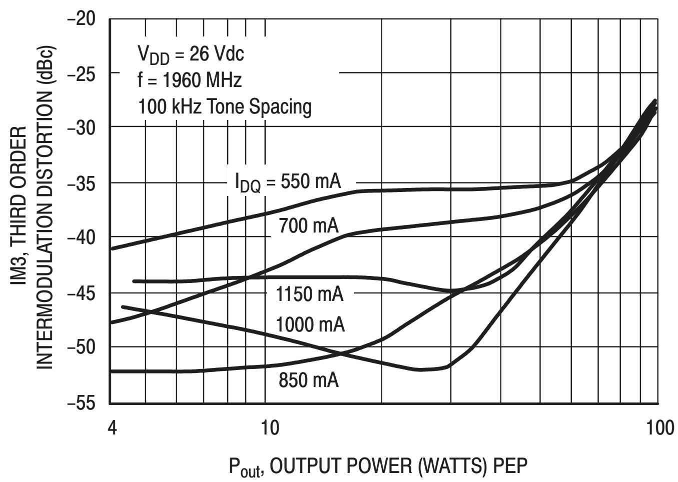


Figure 6. Third Order Intermodulation Distortion versus Output Power and I_{DQ}

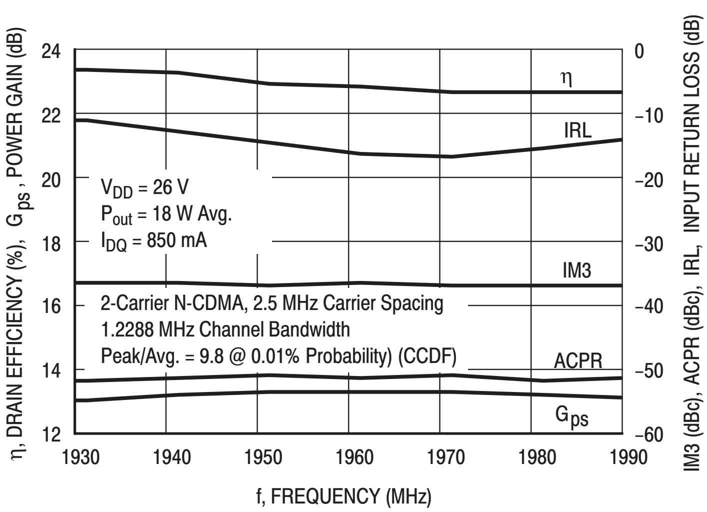


Figure 7. 2-Carrier N-CDMA Broadband Performance

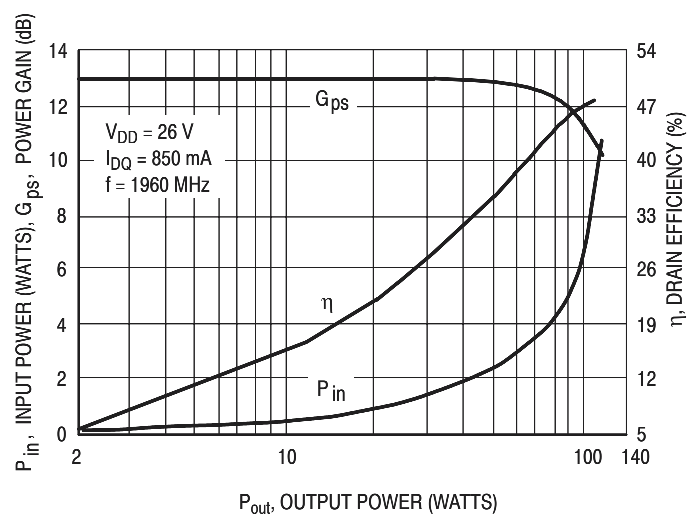


Figure 8. CW Performance

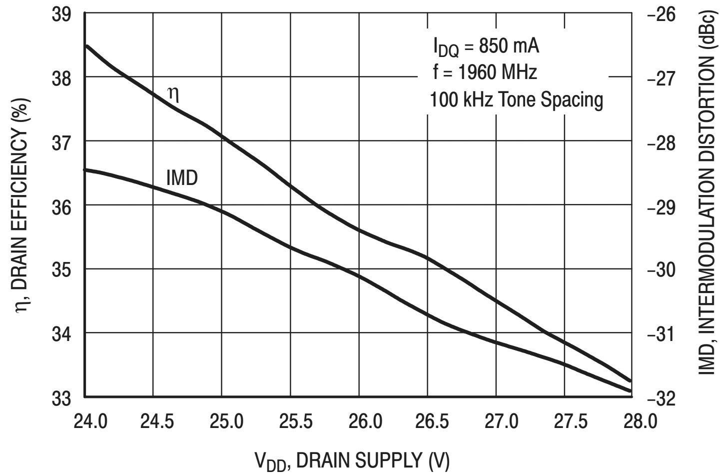


Figure 9. Two-Tone Intermodulation Distortion and Drain Efficiency versus Drain Supply

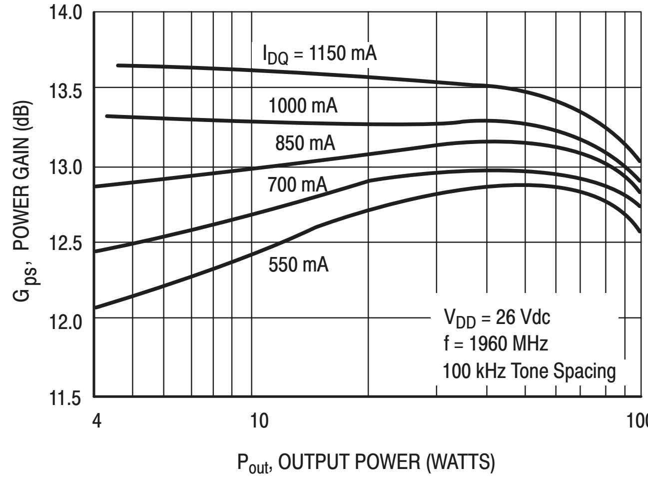


Figure 10. Two-Tone Power Gain versus Output Power

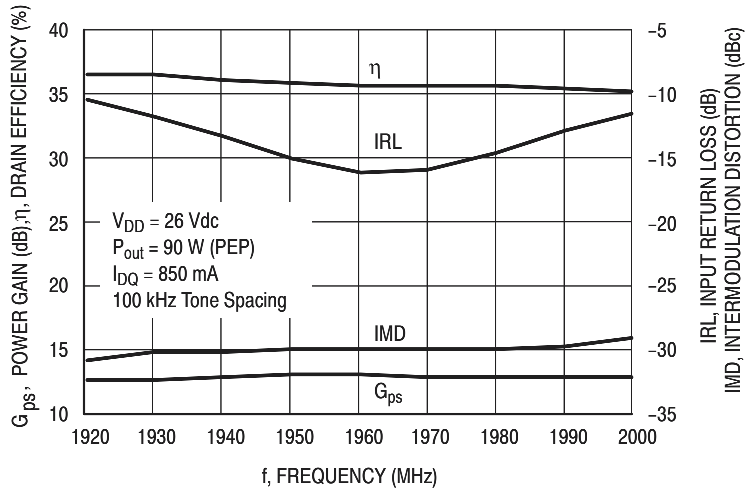
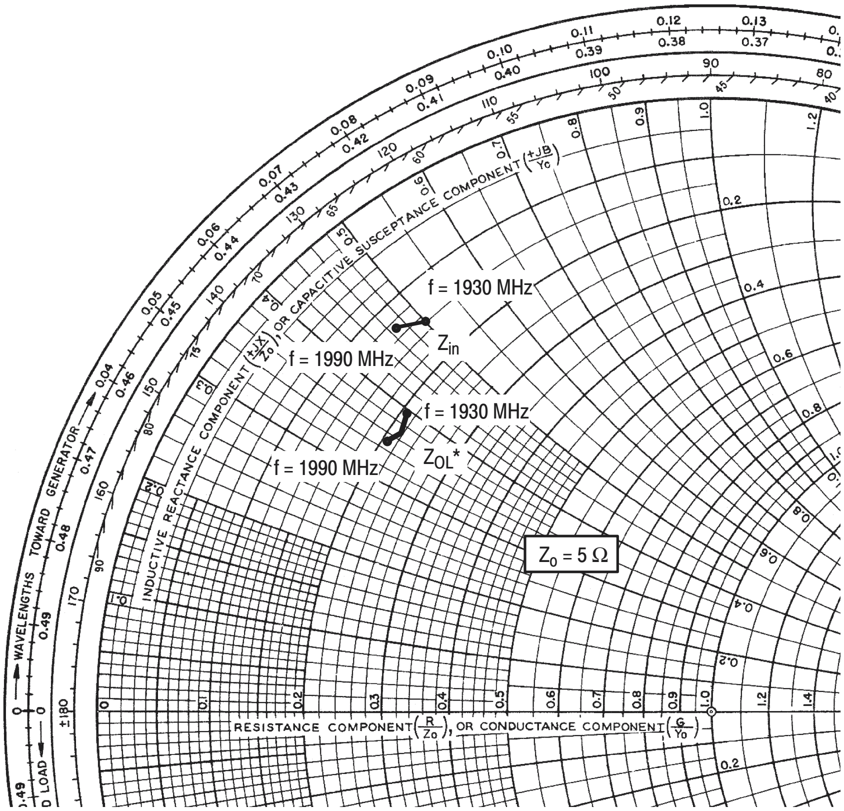


Figure 11. Two-Tone Broadband Performance



V_{DD} = 26 V, I_{DQ} = 850 mA, P_{out} = 18 W Avg.

f MHz	Z_{in} Ω	Z_{OL}* Ω
1930	0.75 + j2.50	1.05 + j1.95
1960	0.70 + j2.40	1.10 + j1.85
1990	0.65 + j2.35	1.05 + j1.75

Z_{in} = Complex conjugate of source impedance.

Z_{OL}* = Complex conjugate of the optimum load impedance at a given output power, voltage, IMD, bias current and frequency.

Note: Z_{OL}* was chosen based on tradeoffs between gain, output power, drain efficiency and intermodulation distortion.

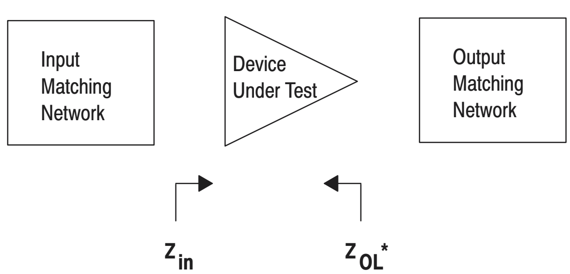
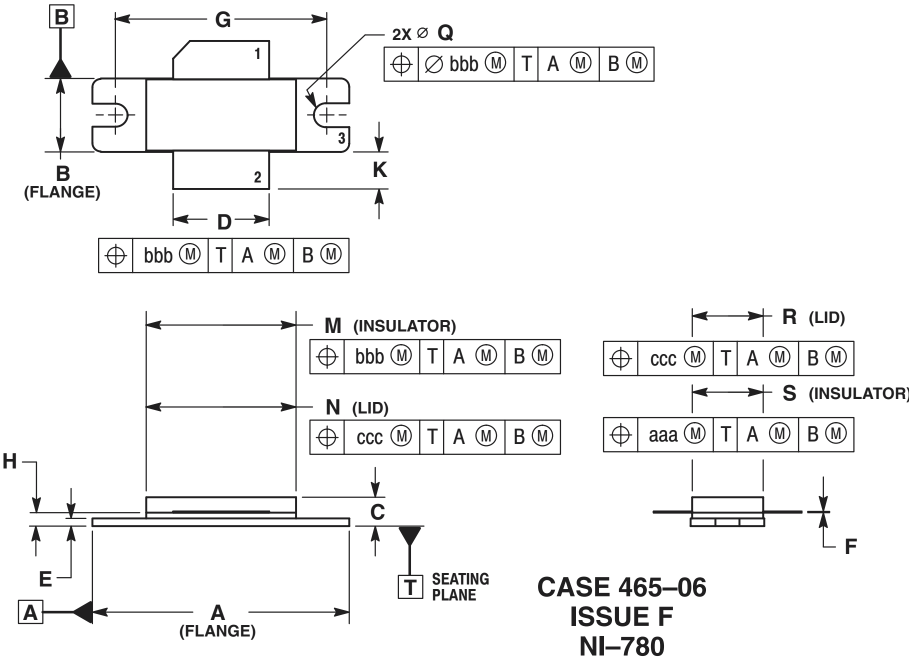


Figure 12. Series Equivalent Input and Output Impedance

NOTES

NOTES

PACKAGE DIMENSIONS

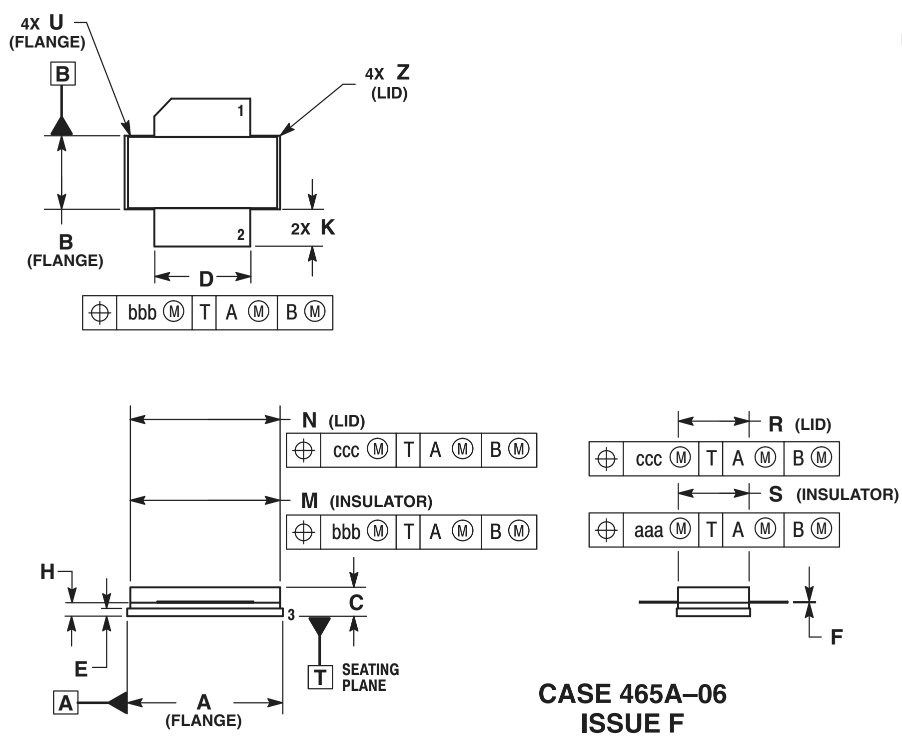


CASE 465–06
ISSUE F
NI–780
MRF19085

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	⌀.118	⌀.138	⌀3.00	⌀3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



CASE 465A–06
ISSUE F
NI–780S
MRF19085SR3, MRF19085LSR3

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:
PIN 1. DRAIN
2. GATE
5. SOURCE

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JAPAN: Motorola Japan Ltd.; SPS, Technical Information Center, 3–20–1, Minami–Azabu. Minato–ku, Tokyo 106–8573 Japan. 81–3–3440–3569

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Centre, 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong. 852–26668334

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